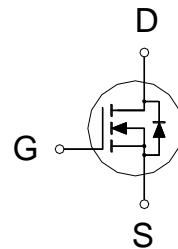


NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK5X8BA**
PDFN 5x6P
Halogen-Free & Lead-Free**PRODUCT SUMMARY**

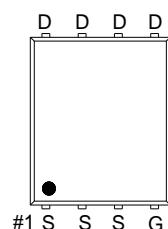
$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
40V	5.6mΩ	67A

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.



G. GATE
D. DRAIN
S. SOURCE
100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ⁴	$T_C = 25^\circ\text{C}$	I_D	67	A
	$T_C = 100^\circ\text{C}$		42	
Pulsed Drain Current ¹		I_{DM}	164	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	16	
	$T_A = 70^\circ\text{C}$		13	
Avalanche Current		I_{AS}	54	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	145	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	50	W
	$T_C = 100^\circ\text{C}$		20	
Power Dissipation ³	$T_A = 25^\circ\text{C}$	P_D	3	
	$T_A = 70^\circ\text{C}$		1.9	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK5X8BA
PDFN 5x6P
Halogen-Free & Lead-Free****THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		41	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		54	
Junction-to-Case	Steady-State	$R_{\theta JC}$		2.5	

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.**ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.9	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
		$V_{DS} = 40V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ⁴	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 16A$		6	8.5	$m\Omega$
		$V_{GS} = 10V, I_D = 20A$		4.6	5.6	
Forward Transconductance ⁴	g_{fs}	$V_{DS} = 5V, I_D = 20A$		91		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 20V, f = 1MHz$		2861		pF
Output Capacitance	C_{oss}			427		
Reverse Transfer Capacitance	C_{rss}			244		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.1		Ω
Total Gate Charge ⁵	Q_g	$V_{GS} = 10V$		51		nC
				26		
Gate-Source Charge ⁵	Q_{gs}	$V_{DS} = 20V, V_{GS} = 10V, I_D = 20A$		9		nC
Gate-Drain Charge ⁵	Q_{gd}			12		
Turn-On Delay Time ⁵	$t_{d(on)}$	$V_{DS} = 20V, I_D \approx 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		18		nS
Rise Time ⁵	t_r			85		
Turn-Off Delay Time ⁵	$t_{d(off)}$			58		
Fall Time ⁵	t_f			93		

NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK5X8BA**

PDFN 5x6P

Halogen-Free & Lead-Free

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)

Continuous Current	I_S				38	A
Forward Voltage ⁴	V_{SD}	$I_F = 20\text{A}, V_{GS} = 0\text{V}$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A} / \mu\text{s}$	19			nS
Reverse Recovery Charge	Q_{rr}		11			nC

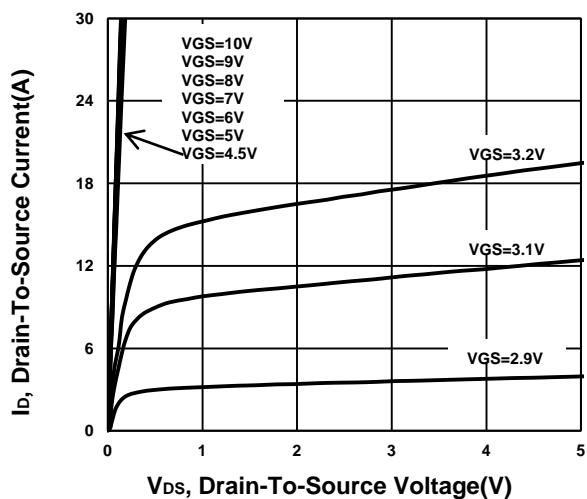
⁴Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.⁵Independent of operating temperature.

NIKO-SEM

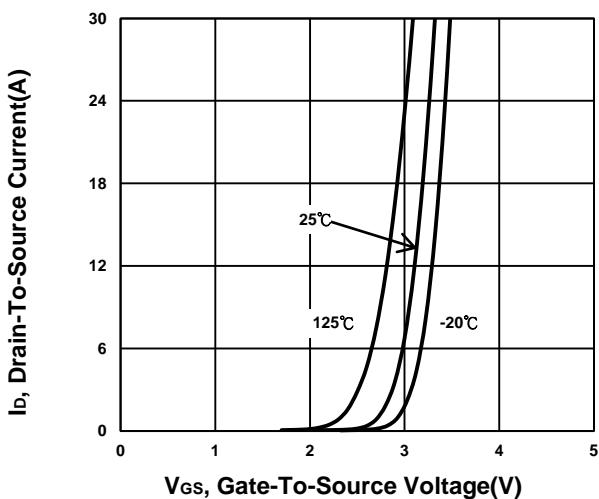
**N-Channel Enhancement Mode
Field Effect Transistor**

PK5X8BA
PDFN 5x6P
Halogen-Free & Lead-Free

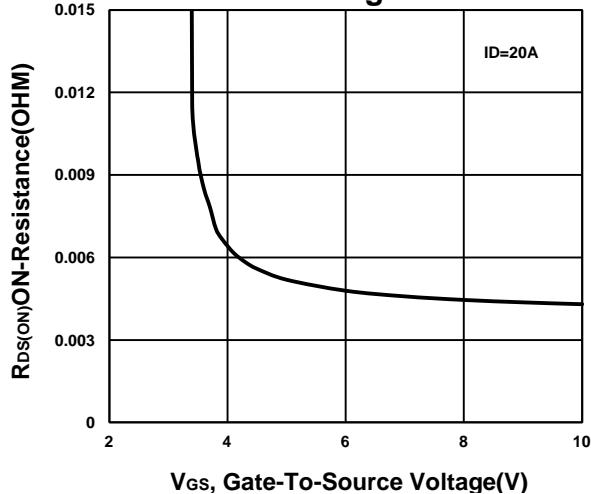
Output Characteristics



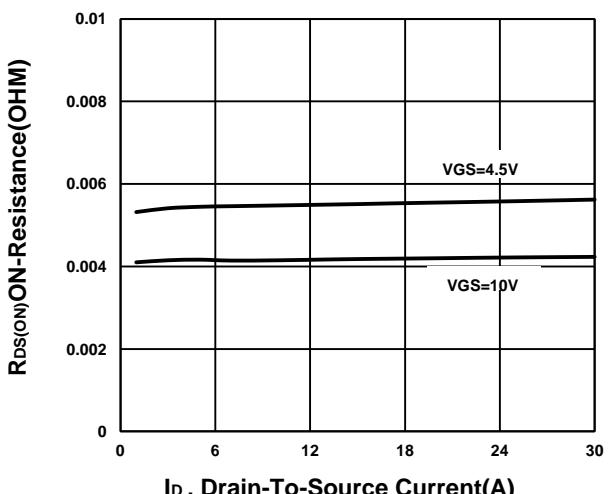
Transfer Characteristics



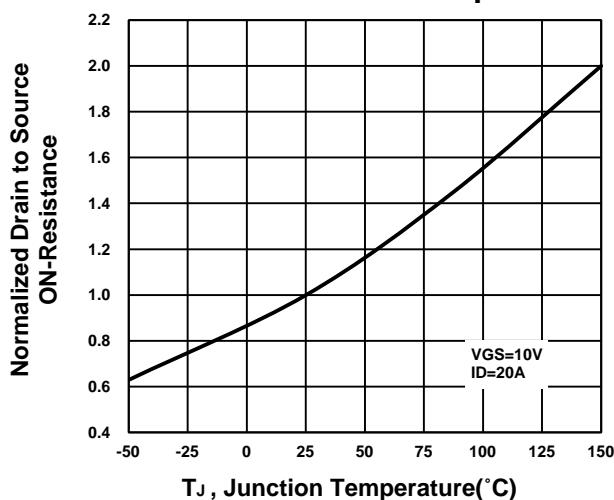
On-Resistance VS Gate-To-Source Voltage



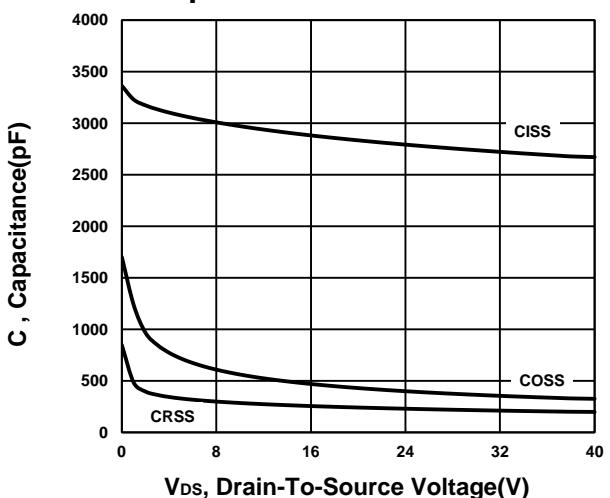
On-Resistance VS Drain Current

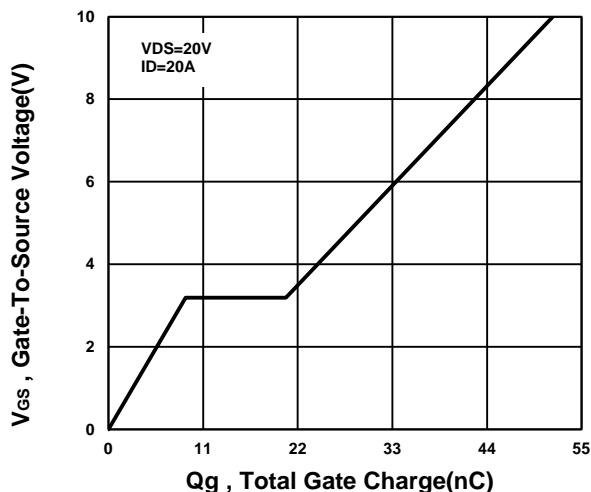
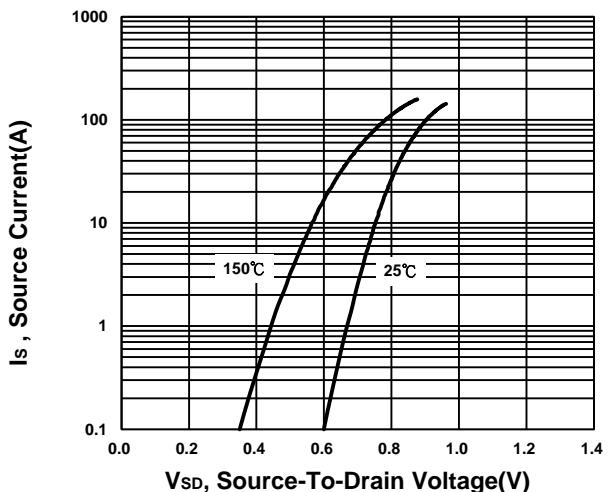
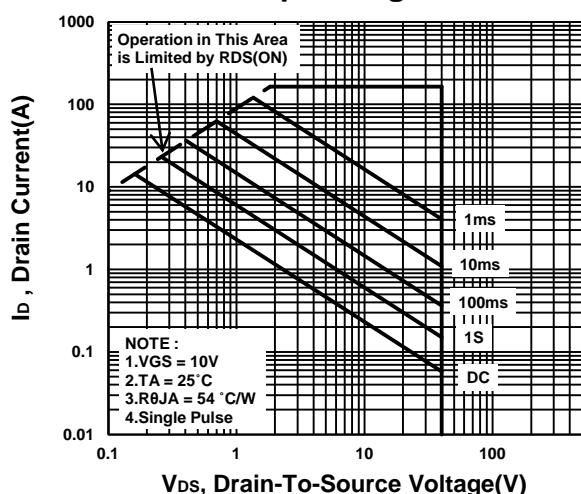
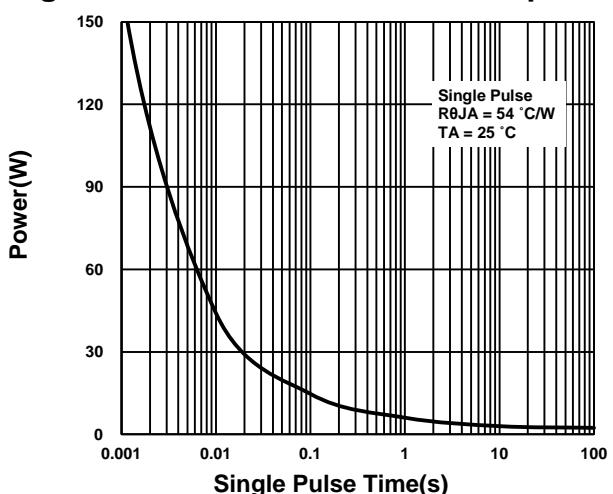
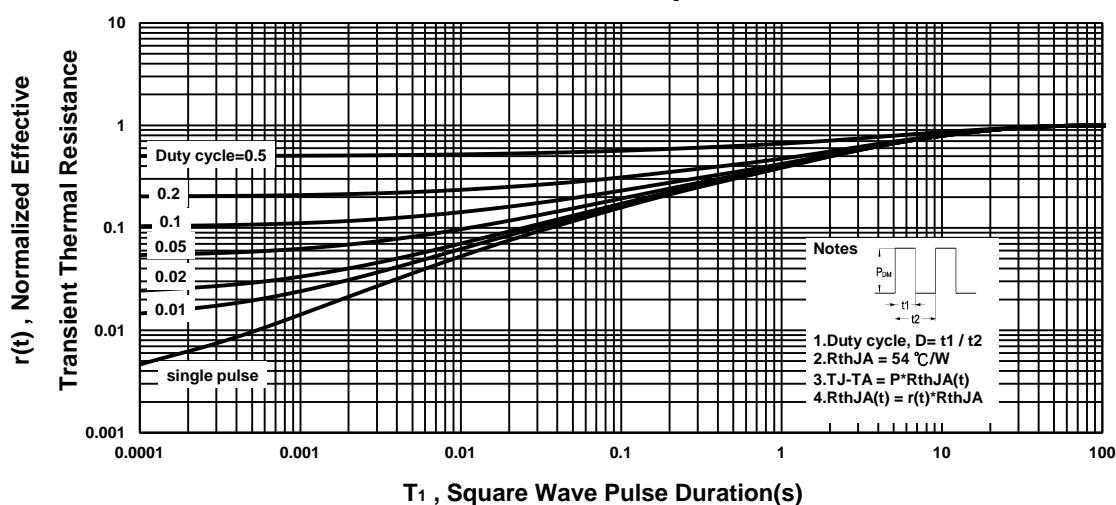


On-Resistance VS Temperature



Capacitance Characteristic



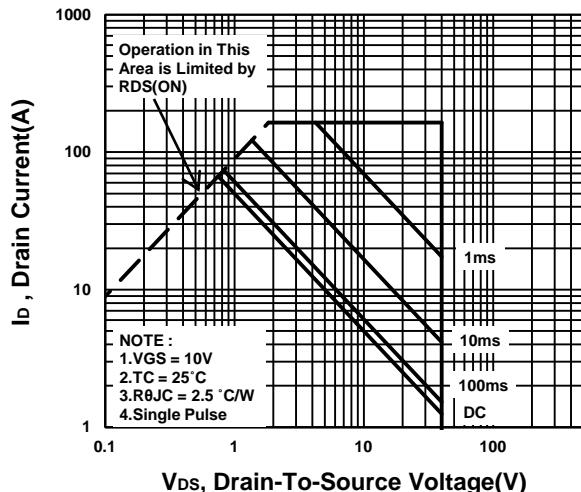
NIKO-SEM**N-Channel Enhancement Mode
Field Effect Transistor****PK5X8BA
PDFN 5x6P
Halogen-Free & Lead-Free****Gate charge Characteristics****Source-Drain Diode Forward Voltage****Safe Operating Area****Single Pulse Maximum Power Dissipation****Transient Thermal Response Curve**

NIKO-SEM

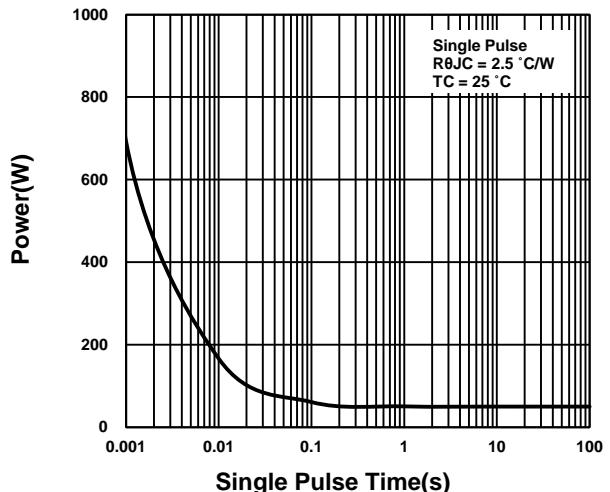
**N-Channel Enhancement Mode
Field Effect Transistor**

PK5X8BA
PDFN 5x6P
Halogen-Free & Lead-Free

Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

